arXiv:1206.3780v1 [cond-mat.mtrl-sci] 17 Jun 2012

Detailed analysis of the performance of the modified Becke-Johnson potential

J. A. Camargo-Martínez and R. Baquero
Departamento de Física, CINVESTAV-IPN, Av. IPN 2508, 07360 México

(Dated: March 8, 2013)

Abstract

Very recently, in the 2011 version of the Wien2K code, the long standing short come of the codes based on Density Functional Theory, namely, its impossibility to account for the experimental band gap value of semiconductors, was overcome. The novelty is the introduction of a new exchange and correlation potential, the modified Becke-Johnson potential (mBJLDA). In this letter, we report our detailed analysis of this recent work. We calculated using this code, the band structure of forty one semiconductors and found an important improvement in the overall agreement with experiment as Tran and Blaha [*Phys. Rev. Lett.* 102, 226401 (2009)] did before for a more reduced set of semiconductors. We find, nevertheless, within this enhanced set, that the deviation from the experimental gap value can reach even much more than 20%, in some cases. Furthermore, since there is no exchange and correlation energy term from which the mBJLDA potential can be deduced, a direct optimization procedure to get the lattice parameter in a consistent way is not possible as in the usual theory. These authors suggest that a LDA or a GGA optimization procedure is used previous to a band structure calculation and the resulting lattice parameter introduced into the 2011 code. This choice is important since small percentage differences in the lattice parameter can give rise to quite higher percentage deviations from experiment in the predicted band gap value. We found that by using the average of the two lattice parameters (LDA and GGA) a better agreement with the band gap experimental value is systematically obtained. As a rule, the LDA optimization underestimates the lattice parameter while the GGA one overestimates it. Also we found that using the experimental lattice parameter instead, surprisingly high deviations of the predicted band gap value from experiment, occur. This is an odd result since, in general, the quality of the LDA and GGA obtained lattice parameters are judged to be as good as their proximity to the experimental lattice parameter value. This judgement implies the idea that the best result for the predicted band gap value is obtained when the closest-to-experiment lattice parameter is used. On the other hand, the band structure calculated with the mBJLDA potential seems, at first sight, a simple rigid displacement of the conduction bands towards higher energies. A closer look reveals that, in some cases, important differences occur that might not be negligible in certain systems containing a semiconductor as it might happen at interfaces. So, in some systems containing a semiconductor, neither the direct use of the Wien2k previous version nor its use with a rigid displacement of the conduction bands added so as to reproduce the band gap value, are totally reliable. We conclude that, in spite of the very important improvement in the band gap agreement with experiment using the new mBJLDA potential, there are issues that point to the fact that this problem is not yet totally closed.

I. INTRODUCTION

Wien2k [1] has been one of the most used codes to calculate the band structure of solids since long ago. In 2011, the long standing short come, i.e., its impossibility to reproduce the experimental gap of semiconductors, has been overcome in the Wien2k 2011 version [2]. This code is based on the Full Potential (Linearized) augmented plane waves and local orbitals [FP-(L)APW+lo] [3] where a new exchange and correlation potential was introduced. The result is a very remarkable improvement with respect to the previous version. Some cases worth noting remain as an exception but the overall agreement is good. While computing the gap of a certain number of semiconductors (41), we found that optimization plays a role since small differences in the lattice parameter can give, for the same semiconductor, noticeable differences in the gap. It was observed that small changes in the lattice parameter between 0.02% and 1.0%, can induce considerable differences in the gap between 0.5% and 6.5% (see text below) The optimization procedure gives the value of the lattice parameter that is consistent with the minimum of the energy vs. volume curve. As such, it depends on the interchange and correlation energy, E_{xc}, used in the calculation. In principle, it appears that the consistent procedure should be to use in the optimization procedure from which the lattice parameter is obtained, the exchange and correlation energy functional from which the exchange and correlation potential to be used in the electronic band structure is deduced. The previous version of the Wien2K code uses either LDA or GGA in this way but as it is well known, neither formulation reproduces accurately enough the gap of semiconductors. The new exchange and correlation potential, the modified Becke-Johnson potential (mBJLDA), does a much better job. Blaha et al. [2] got the best results when the lattice parameter is first obtained from a LDA or a GGA optimization followed by a band structure calculation using the new mBJLDA exchange and correlation potential. This way of performing the calculation is necessary since it is impossible to obtain an expression for a functional E_{xc} such that the mBJLDA potential is $V_{mBJ} = \delta E_{xc}/\delta\rho$. as in the usual theory. In this work, we analyse the results obtained with the new code to pinpoint to its assets and to its odds in more detail. We conclude that even though the overall agreement with experiment of the band gap value obtained with the new code constitutes a noticeable improvement, there are some cases and details that point to the fact that the problem might not be really totally closed.

II. DENSITY FUNCTIONAL THEORY

Several codes were developed based on Density Functional Theory (DFT) which became the most used, precise and practical way to calculate the band structure of solids. The development of practical approximations to the exchange and correlation energy functional lead to a remarkable degree of accuracy to describe even complicated metallic systems. At the basis of DFT is the Hohenberg-Khon theorem [4] which shows that the knowledge of the density of the ground state is equivalent to the one of the wave function itself. The density of states of the real ground state many body system is equal to the one calculated from the solution of the Khon-Sham equations [5],

$$[T + V_H + V_{xc}]\varphi_i(r) = \varepsilon_i \varphi_i \tag{1}$$

where the density is calculated taking into account the occupied states only. In eq.(1), T is the kinetic energy operator, V_H is the Hartree potential and V_{xc} is the exchange and correlation potential which is calculated from the exchange and correlation energy functional; $V_{xc}(r) = \frac{\delta E_{xc}[\rho]}{\delta\rho}$. To solve the Khon-Sham equations (1), an explicit expression for $E_{xc}[\rho]$ is needed. The exact expression is unknown since it includes all kind of correlations between all the particles in the system. So an approximation is needed. The first and best known approximation is the Local Density Approximation, LDA [6], which was followed by the Generalized Gradient Approximation (GGA) [7] and the meta-GGA [7] among others. These potentials reproduce rather well the band structure of even complicated metallic systems but fail to reproduce the gap of semiconductors. To solve this problem, Blaha et al. [2] have reported the mBJLDA potential which is a modification of the exchange and correlation potential of Becke and Johnson (BJ) [8]. The new potential reproduces the experimental gap of semiconductors with accuracy several orders of magnitude better than the previous version of the Wien2K code using either the LDA or the GGA. The mBJLDA potential is

$$V_{x,\sigma}^{MBJ}(r) = cV_{x,\sigma}^{BR}(r) + (3c-2)\frac{1}{\pi}\frac{\sqrt{5}}{12}\frac{\sqrt{2t_\sigma(r)}}{\rho_\sigma(r)} \tag{2}$$

Where $\rho_\sigma(r)$ is the spin dependent density of states, $t_\sigma(r)$ is the kinetic energy density and $V_{x,\sigma}^{BJ}(r)$ is the Becke-Roussel potential (BR) [9]. The c stands for

$$c = \alpha + \left(\beta\frac{1}{V_{cell}}\int d^3r\frac{\mid\nabla\rho(r)\mid}{\rho(r)}\right)^{1/2} \tag{3}$$

α and β are free parameters. The *Wien2k 2011* code defines $\alpha = -0.012$ and $\beta = 1.023\ Bohr^{1/2}$. These values are general but certainly fixed experimenting with several cases. No expression for the exchange and correlation energy is given and therefore no total energy functional is really possible. It is in this sense that the new formulation might be seen as a semi-empirical model in spite of its universality. We next explore further some details of this new formulation.

III. THE OPTIMIZATION PROCEDURE

The Wien2k code allows the calculation of the equilibrium structural properties of the system, the minimum of the total energy, (E_0), the Bulk modulus, (B_0), its derivative with respect to pressure, (B_0'), and the equilibrium volume at zero pressure, V_0, by fitting the data to an equation of state (EOS). The code uses either the EOS by Murnaghan [10] or the one by Birch-Murnaghan [11] or else the so-called EOS2 [12]. We used the first one,

$$E(V) = E_0 + \frac{B_0 V}{B_0'}\left[\frac{1}{(B_0'-1)}\left(\frac{V_0}{V}\right)^{B_0'} + 1\right] - \frac{B_0 V_0}{(B_0'-1)} \tag{4}$$

$$P(V) = \frac{B_0}{B_0'}\left[\left(\frac{V_0}{V}\right)^{B_0'} - 1\right] \tag{5}$$

and performed the calculation for some semiconductors (Si, Ge, AlAs, SiC, BP, AlP, GaN and GaAs) and some dielectrics (LiF, MgO and BN), using the LDA, the GGA and the new mBJLDA potential formulation.

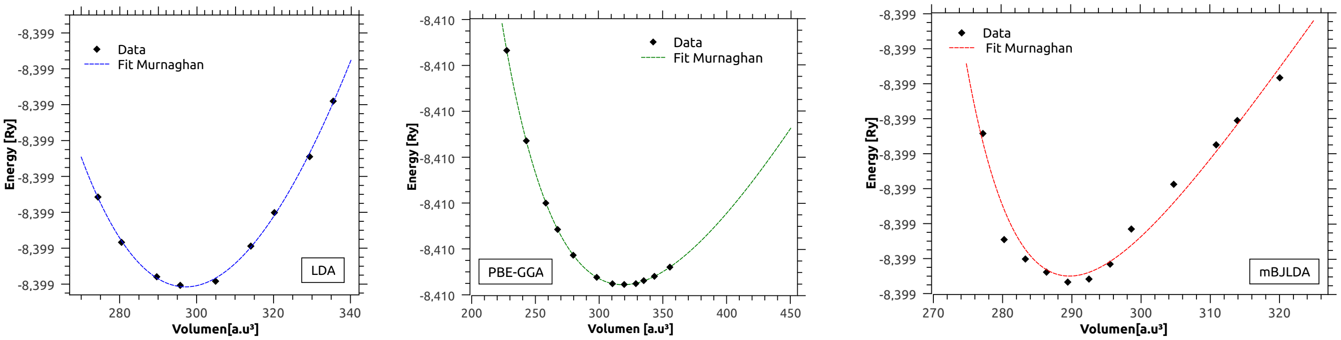

FIG. 1. Energy vs. volume curve for GaAs using the LDA, GGA and the mBJLDA potential formulation. The curves are the Murnaghan fit. The points are the results of our calculation..See text.

In Fig. 1, we show our calculated energy vs. volume results and the curves fitted to the Murnaghan EOS for GaAs. It is clear from Fig.1, that in the case of the mBJLDA procedure (no correlation and exchange energy term) the fit is quite uncertain since the data do not actually follow Murnaghan's curve in sharp contrast with the LDA and the GGA. The same picture arises from the calculations made in the rest of the cases that we deal with in this work. We present in Tables I and II, the fitting parameters to eq.(4). We can see in Table I, that when calculated with the LDA, the deviations from experiment of the Bulk modulus and its derivative oscillate roughly between 1-12%; with the GGA between 4-18%. With the mBJLDA procedure (no exchange and correlation energy) the numbers obtained have no sense at all. The values for the Bulk modulus as compared to experiment are overestimated in all cases but three (Si, Ge, AlAs) when an LDA optimization is used. For an GGA one, all are underestimated but two (LiF, BN). The GGA optimization gives a better agreement with experiment in five of the eleven semiconductors considered (MgO, LiF, AlP, BN, GaN). Looking at the derivative of the Bulk modulus with respect to pressure (seven experimental results reported), the GGA optimization gives a better agreement with experiment in four cases (Si, Ge, MgO, GaN).

In Table II, we present the minimum of the Total Energy, E_0, and the lattice Parameter, a, calculated with LDA, GGA, its average value (a_{Avg}) and experimental reports at low temperature (LT) and at room temperature (RT). It is worth noting that the problem with the mJBLDA procedure comes from its inability to account for the derivative of the energy vs. volume curve at the minimum but not from the value itself or from the position of the minimum from which the lattice parameter is calculated. We found this to be a general feature of all the solids that we studied

TABLE I. The Bulk modulus, (B_0), in GPa and its derivative, (B_0'), as obtained from the Murghanan fit. The crystal structure is shown in parenthesis. Experimental values were taken from the references [13–23].

	LDA		GGA		mBJLDA		Expt.	
Solid	B_0	B_0'	B_0	B_0'	B_0	B_0'	B_0	B_0'
C(A1)	434.34	3.69	432.52	3.99	897.67	28.70	442	4.03
Si(A1)	92.96	4.35	87.71	4.23	341.75	35.65	97.82	4.09
Ge(A1)	73.18	4.98	62.45	3.93	181.25	24.08	75.80	4.55
MgO(B1)	175.52	4.61	149.89	4.18	119.89	0.10	160.00	4.15
LiF(B3)	69.29	4.91	68.07	4.22	1388.48	28.20	62.00	5.14
AlAs(B3)	73.34	4.78	67.29	4.53	452.36	55.03	78.10	-
SiC(B3)	233.85	4.06	214.95	4.11	1116.31	50.25	224.00	4.1
BP(B3)	175.12	3.85	160.91	3.84	746.17	34.91	173.00	3.76
AlP(B3)	89.70	4.17	82.15	3.97	392.67	38.73	86.00	3.99
BN(B3)	401.27	3.71	370.10	3.66	3279.96	43.95	369.00	4.00
GaN(B3)	202.45	3.28	177.39	4.11	694.15	31.79	188.00	3.2
GaAs(B3)	75.15	3.97	67.14	4.03	320.05	41.98	74.66	4.6

in this work. It is necessary to emphasize that the Murghanan fit is very disputable in this case and that we have extracted a minimum value for the energy and for the position of the minimum (equilibrium volume) even though the curve itself is not totally justifiable. Our observations in this point are made "modulus" this remark. Since in the mBJLDA procedure, the optimization does not contain a term for the exchange and correlation energy, the fact that the lattice parameter that results does not deviate very much from experiment (see Table II, calculated for only eleven compounds) means that the contribution of this term to the total energy at the equilibrium volume might be actually small although important to fix the bulk modulus and its derivative. Notice that the LDA gives rise to deviations of the lattice parameter that are always below the experimental value (except for the values of a in hexagonal structures) while exactly the contrary arises with the GGA (except for the values of c in hexagonal structures). GGA results in a shift towards higher values of the equilibrium volume which might be thought as a kind of relaxation due to the use of derivatives of the local density in the functional. The experimental lattice parameters, a, were taken from refs. [23–25].

In Table II, we first compare the lattice parameter, a, obtained with an LDA optimization to experimental data taken at low temperature (LT) and at room temperature (RT). In the first case, we find, in general, small differences (0.6-1%), except for CuBr and CuCl (2.6 and 3.7, respectively). In the second case, the differences are usually below 1.3% but can rise up to 3.9% as in CuCl. If we use the GGA approximation the differences are slightly higher in general. Even though the optimization with the mBJLDA potential is not really acceptable, if we force a result by taking the minimum of the Murnaghan curve, we come out with values of the lattice parameter that are up to 2.7% off comparing to the RT experimental values (see Table II).

At first sight, it seems that, in spite of the wrong results for the Bulk modulus and its derivative with respect to pressure, the lattice parameters that are the output of an optimization procedure that ignores the exchange and correlation energy term as it is compulsory in the mBJLDA procedure, are not unreasonable. Tran and Blaha [2] found that the correct procedure is to start with an GGA (or LDA) optimization and to introduce the lattice parameter value obtained into the band structure calculation code that uses the new potential.

TABLE II. Minimum of Total energy, (E_0), and lattice parameters, (a), obtained from the Murnaghane a_{Avg} values are the average value between a_{LDA} and a_{GGA}. The experimental data, at low temperature (LT) and room temperature (RT), are from refs. [23–25].

	Minimum of Total energy $E_0[Ry]$			Lattice parameters $a[\AA]$						
Solid	LDA	GGA	mBJLDA		a_{mBJLDA}	a_{LDA}	a_{GGA}	a_{Avg}	$a_{LT}^{Expt.}$	$a_{RT}^{Expt.}$
C(A1)	-151.19	-152.53	-151.09		-	3.5339	3.5731	3.5535	3.5667*	3.5668
Si(A1)	-1156.16	-1160.14	-1156.07		5.3421	5.4073	5.4738	5.4406	5.4298*	5.4310
Ge(A1)	-8384.72	-8396.35	-8384.50		5.5012	5.6269	5.7586	5.6928	5.6524*	5.6579
MgO(B1)	-548.93	-551.43	-548.64		4.3159	4.1635	4.2569	4.2102	4.2052*[a]	4.2110
LiF(B3)	-213.82	-215.10	-213.49		3.9432	3.9152	4.0710	3.9931	-	4.0300
AlAs(B3)	-5000.04	-5007.89	-4999.88		5.5847	5.6329	5.7304	5.6817	5.6605*	5.6614
SiC(B3)	-653.75	-656.31	-653.63		4.3393	4.3378	4.3944	4.3661	4.3585^{b}_{3K}	4.3596
BP(B3)	-731.34	-733.96	-731.25		4.4727	4.4937	4.5510	4.5224	-	4.5383
AlP(B3)	-1165.95	-1169.93	-1165.84		5.3861	5.4371	5.5110	5.4741	-	5.4635
BN(B3)	-158.24	-159.39	-158.10		3.5527	3.5831	3.6268	3.6050	-	3.6155
GaN(B3)	-3991.53	-3997.83	-3991.25		4.4609	4.4663	4.5626	4.5145	-	4.5230
GaAs(B3)	-8398.82	-8410.46	-8398.60		5.5460	5.6050	5.7401	5.6726	5.6523*	5.6533
BAs(B3)	-4565.37	-4571.86	-4565.23		-	4.7314	4.8085	4.7700	-	4.777
InP(B3)	-12435.27	-12450.79	-12438.09		-	5.8239	5.9535	5.8887	$5.86574_{4.8K}$	5.87875
AlSb(B3)	-13440.20	-13452.93	-13440.06		-	6.1084	6.2209	6.1647	-	6.1355
GaSb(B3)	-16839.02	-16855.53	-16838.80		-	6.0449	6.2086	6.1268	-	6.09593
GaP(B3)	-4564.73	-4572.49	-4564.55		-	5.3912	5.5084	5.4498	5.4469*	5.4508
InAs(B3)	-16272.42	-16288.81	-16272.41		-	6.0185	6.1804	6.0995	-	6.0584
InSb(B3)	-24712.60	-24733.86	-24712.38		-	6.4497	6.6363	6.5430	-	6.4794
CdS(B3)	-11978.10	-11977.82	-11990.53		-	5.7636	5.9304	5.8470	-	5.8320
CdTe(B3)	-24764.62	-24785.90	-24764.36		-	6.4166	6.6198	6.5182	6.4675[c]	6.4810
CdSe(B3)	-16036.25	-16052.59	-16035.95		-	6.0169	6.1995	6.1082	-	6.0770
ZnS(B3)	-4383.03	-4390.75	-4382.78		-	5.3083	5.4524	5.3804	-	5.4102
ZnSe(B3)	-8441.16	-8452.81	-8440.88		-	5.5826	5.7401	5.6614	-	5.6680
ZnTe(B3)	-17169.53	-17186.11	-17169.30		-	6.0129	6.1854	6.0992	-	6.0890
MgS(B1)	-1195.27	-1199.27	-1195.11		-	5.1358	5.2342	5.1850	-	5.2030
MgS(B3)	-1195.26	-1199.27	-1195.08		-	5.5985	5.7018	5.6502	-	5.6220
MgSe(B1)	-5253.40	-5261.32	-5253.23		-	5.3993	5.5129	5.4561	-	5.4600
MgTe(B3)	-13981.75	-13994.61	-13981.59		-	6.3836	6.5187	6.4512	-	6.4230
BaS(B1)	-17062.58	-17077.46	-17062.35		-	6.2743	6.4313	6.3528	-	6.3890[d]
BaSe(B1)	-21120.74	-21139.53	-21120.49		-	6.4792	6.6604	6.5698	-	6.5950[d]
BaTe(B1)	-29849.11	-29872.83	-29848.91		-	6.8647	7.0680	6.9664	-	7.0070[d]
CaO(B1)	-1507.48	-1511.80	-1507.19		-	4.7177	4.8346	4.7762	-	4.8110
CuCl(B3)	-4225.41	-4233.11	-4225.12		-	5.2101	5.4403	5.3252	5.4093*[a]	5.4202
CuBr(B3)	-8511.70	-8523.37	-8511.40		-	5.5264	5.7391	5.6328	5.6764*	5.6900
AgF(B1)	-10823.54	-10834.37	-10823.05		-	4.7946	5.0224	4.9085	-	4.9360
AgI(B1)	-24851.50	-24872.79	-24851.18		-	6.3656	6.6416	6.5036	-	6.4990
GaN(B4)	-7983.05	-7995.65	-7982.47	a	-	3.2027	3.2051	3.2039	-	3.1980
				c	-	5.1408	5.1330	5.1369	-	5.1850
InN(B4)	-23730.09	-23729.59	-23752.21	a	-	3.5715	3.5751	3.5733	-	3.5480
				c	-	5.6845	5.6729	5.6787	-	5.7600
AlN(B4)	-1185.41	-1190.73	-1185.32	a	-	3.1200	3.1211	3.1206	3.1113*[e]	3.1120
				c	-	4.9565	4.9529	4.9547	4.9793*[e]	4.9820
ZnO(B4)	-7473.30	-7485.65	-7473.17	a	-	3.2675	3.2604	3.2640	$3.2482^{f}_{4.2K}$	3.2500
				c	-	5.1736	5.1653	5.1695	$5.2040^{f}_{4.2K}$	5.2070

*Extrapolated values. [a]Ref. [26], [b]Ref. [27], [c]Ref. [28], [d]Ref. [29], [e]Ref. [30], [f]Ref. [31]

From Table II we further notice that the use of the average lattice parameter, a_{Avg}, ($a_{Avg} = (a_{LDA} + a_{GGA})/2$), results in a gap value that is always in better agreement with experiment. We give an error statistics analysis of this result in Table III to emphasise its validity. To obtain a_{Avg} has a low computational extra cost.

TABLE III. Lattice parameter error statistics for compounds of Table II, in Å.

Error relative to LT experiments.			
	a_{LDA}	a_{GGA}	a_{Avg}
ME[a]	-0.046	0.047	0.00041
MAE[b]	0.050	0.055	0.025
SD[c]	0.046	0.049	0.034
Error relative to RT experiments.			
	a_{LDA}	a_{GGA}	a_{Avg}
ME[a]	-0.055	0.055	-0.00009
MAE[b]	0.058	0.066	0.026
SD[c]	0.048	0.055	0.034

[a] Mean error. [b] Mean absolute error.

[c] Standard deviation.

IV. BAND STRUCTURE CALCULATIONS

In Fig.2, we compare the band structure for Si, Ge, GaAs and LiF calculated with the LDA and with the mBJLDA potential. As a general result, this potential causes a rigid displacement of the conduction bands toward higher energies with respect to the top of the valence band with small differences in the dispersion at some regions of the Brillouin zone but reproducing, in general, the characteristic behavior of the bands for each semiconductor according to experiment [23, 24, 32, 33] as the Wien2k code used to. If we look at the resulting band structures in more detail, we see that a rigid displacement of only the conduction bands as to reproduce the mBJLDA predicted gap value will cause some differences in the upper conduction bands although the ones just above the upper gap edge will match quite well with the calculation using the mBJLDA potential. This is roughly true for the first three semiconductors presented in Fig.2. LiF deserves a more detailed discussion. In Fig.3, we show the result of such a displacement. We can see that clear differences arise that might influence a calculation of a system containing LiF as one of its elements. So, we conclude that, in general, a rigid displacement of a band structure calculation with the old formulation of Wien2K will not be accurate enough for certain purposes as it might occur in the calculation of the band structure of certain interfaces containing a semiconductor as one of its elements, for example. The direct use of the previous version of the Wien2K code in this case might not be accurate enough as well.

In Table IV, we show the result of the calculation using the new potential with the a_{LDA}, a_{GGA} and a_{Avg} to survey the respective differences in the gap value as compared to experiment [23–25]. We can see that if we use the lattice parameter from a LDA optimization, mBJ(a_{LDA}), the prediction for the gap deviates by less than 10% for 21 of the 41 semiconductors considered, between 10-20% for 9 of them and more then 20% for the remaining 11 (Ge and GaAs among them). Using GGA, we get 19, 14, and 6, respectively. When using the average value of the two, we get 25, 7,and 7 a result that improves the calculation at relatively low computational cost. There are, nevertheless, two semiconductors that we did not include in the two last cases just presented, MgS(B3) and MgTe. It turns out that both, the calculation using a_{GGA} and a_{Avg} give the wrong result that the gap is indirect while a_{LDA} gives rise to a correct direct gap for both semiconductors and predicts its value with less than 10% deviation in both cases.

Further, to explore the absolute capacity of the mBJLDA potential to predict the gap value correctly, we have used the experimental lattice parameter value at low temperature (a_{LT}) where it existed in the literature to perform the calculation. It is interesting that the result is not as good as one would expect as it can be seen from Table IV. This calculation shows the best that the mBJLDA potential can do, a result that might be important to bear in mind. It looks like that when no data are available, the best result is obtained by taking the average of the lattice parameters resulting from an LDA optimization and a GGA one.

Furthermore, it is interesting to observe that small differences in the lattice parameter can give rise to noticeable differences in the predicted value for the gap. An example of this is Ge. The small differences in the lattice parameters as 0.5% (LDA) gives rise to a 23% deviation of the gap value as compared to experiment. Within the GGA optimiza-

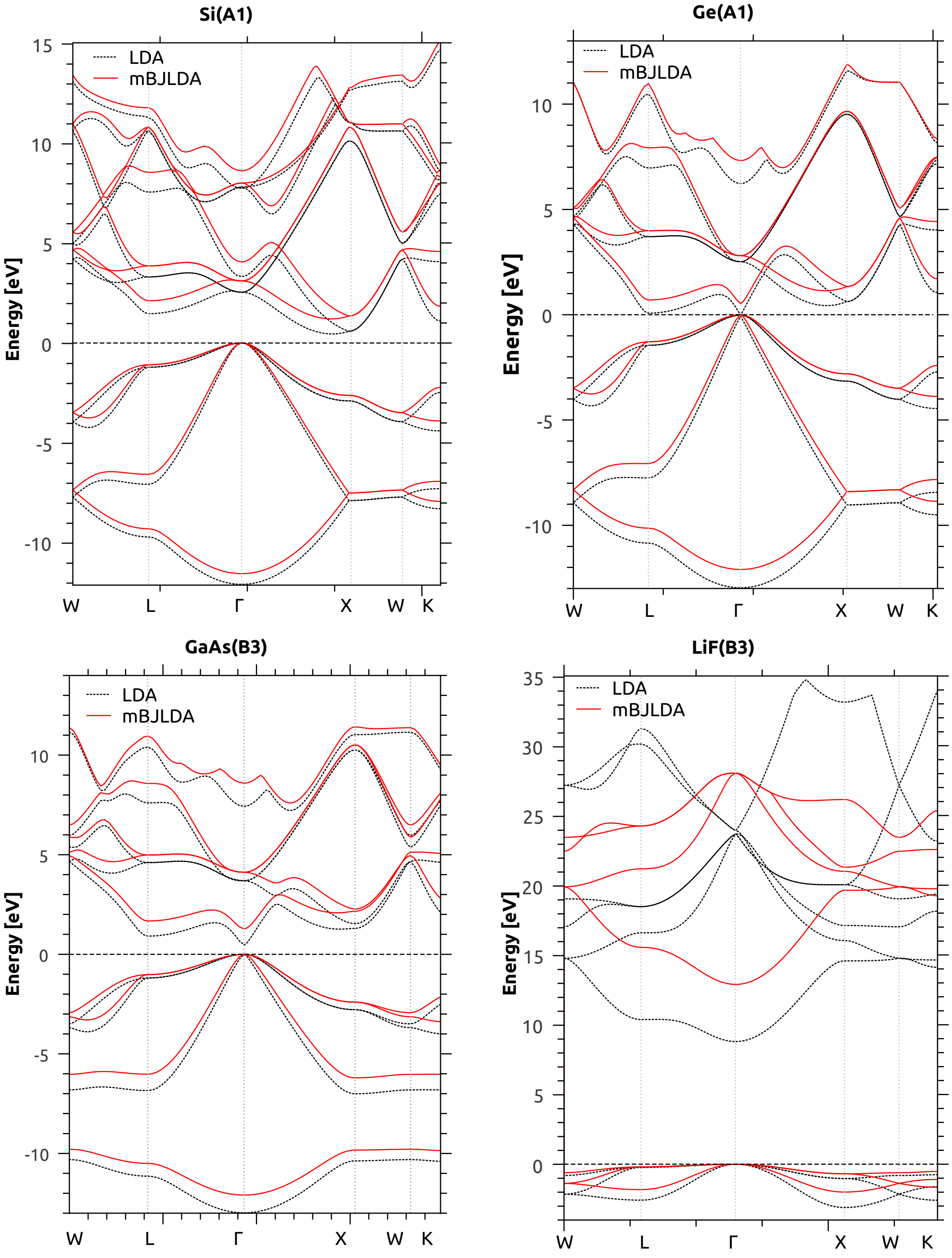

FIG. 2. The band structure obtained for Si, Ge, GaAs, and LiF with LDA and mBJLDA. The origin is at the top of the valence band. In parenthesis the crystal structure is shown.

tion, 1.9% lattice difference generate a 5.4% off value for the gap and a 0.6% difference in the lattice parameter gives an 8.1% difference in the gap when the average is taken. A very interesting issue is that when the experimental value of the lattice parameter is introduced into the mBJLDA code, important deviations from experiment occur. In Table IV, we have included 14 semiconductors for which we found an experimental low temperature lattice parameter value. We get the experimental gap value only for one of them (Si). With less than 10% deviation we found 7 (C, MgO, AlAs, SiC, GaAs, GaP, and CdTe); a deviation between 10-20% occurs in 3 (Ge, InP, and AlN). Very important deviations from experiment occur in CuCl (47.5%), and CuBr (45.3%). These results are facts to bear in mind for a proper

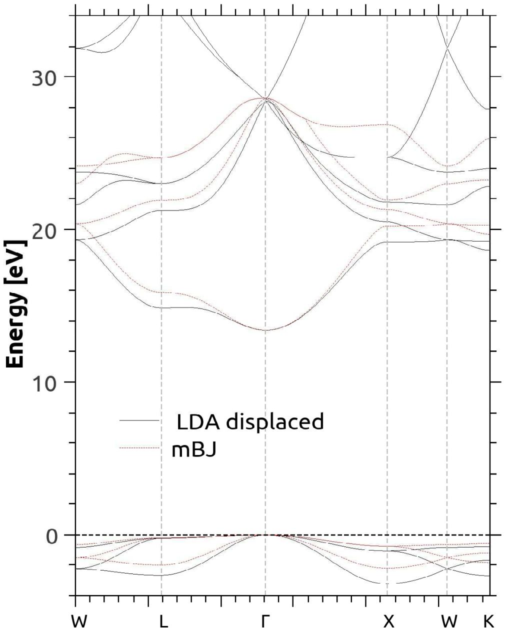

FIG. 3. The band structure obtained for LiF with LDA and mBJLDA.

evaluation of the performance of the mBJLDA potential since the quality of the optimization procedure is judged from the deviation of the predicted lattice parameter from the experimental value. This judgement implies that the best result for the predicted band gap value is obtained when the experimental lattice parameter is introduced into the code. Actually any code should be first of all be examined in this sense so that the selection of an optimization procedure from the deviation of the predicted lattice parameter from experiment really makes sense.

TABLE IV. Calculations of the gap (E_g) in eV, for the potential mBJLDA using parameters in Table II network. The lattice parameter a_{Avg} is the average value between a_{LDA} and a_{GGA}. The experimental values were taken from the references [23–25]. The crystal structure and percentage difference with respect to the experiment is shown in parenthesis.

	Gap				
Solid	$E_g^{mBJ(a_{LDA})}$	$E_g^{mBJ(a_{GGA})}$	$E_g^{mBJ(a_{LT})}$	$E_g^{mBJ(a_{Avg})}$	E_g^{Expt}
C(A1)	4.98 (-9.1%)	4.92 (-10.2%)	4.93 (-10.0%)	4.95 (-9.7%)	5.48*
Si(A1)	1.13 (-3.4%)	1.20 (2.6%)	1.17 (0.0%)	1.17 (0.0%)	1.17*
Ge(A1)	0.91 (23%)	0.70 (-5.4%)	0.84 (13.5%)	0.80 (8.1%)	$0.74_{1.5K}$
MgO(B1)	7.57 (-2.6%)	6.88 (-11.5%)	7.26 (-6.6%)	7.22 (-7.1%)	$7.77_{7.7K}$
AlAs(B3)	2.13 (-4.5%)	2.22 (-0.4%)	2.14 (-4.0%)	2.17 (-2.7%)	2.23_{4K}
SiC(B3)	2.21 (-8.7%)	2.28 (-5.8%)	2.26 (-6.6%)	2.26 (-6.6%)	2.42_{2K}
AlP(B3)	2.28 (-6.9%)	2.37 (-3.3%)	-	2.33 (-4.9%)	2.45_{4K}
GaN(B3)	3.13 (-10.6%)	2.74 (-21.7%)	-	2.94 (-16.0%)	$3.50_{1.6K}$
GaAs(B3)	1.84 (21.1%)	1.28 (-15.8%)	1.62 (6.6%)	1.56 (2.6%)	1.52*
InP(B3)	1.70 (19.7%)	1.34 (-5.6%)	1.59 (12.0%)	1.52 (7.0%)	$1.42_{1.6K}$
AlSb(B3)	1.76 (4.8%)	1.84 (9.5%)	-	1.80 (7.1%)	1.68_{27K}
GaSb(B3)	1.20 (46.3%)	0.68 (-17.1%)	-	0.90 (9.8%)	0.82*
GaP(B3)	2.18 (-7.2%)	2.30 (-2.1%)	2.24 (-4.7%)	2.24 (-4.7%)	2.35*
InAs(B3)	0.77 (83.3%)	0.34 (-19.0%)	-	0.55 (31.0%)	$0.42_{4.2K}$
InSb(B3)	0.59 (145.8%)	0.09 (-62.5%)	-	0.31 (29.2%)	$0.24_{1.8K}$
CdS(B3)	2.68 (8.1%)	2.52 (1.6%)	-	2.61 (5.2%)	$2.48_{4.2K}$
CdTe(B3)	1.80 (12.5%)	1.54 (-3.8%)	1.73 (8.1%)	1.67 (4.4%)	1.60*
CdSe(B3)	1.99 (12.4%)	1.77 (0.0%)	-	1.87 (5.6%)	1.77*
ZnS(B3)	3.85 (1.0%)	3.55 (-6.8%)	-	3.70 (-2.9%)	3.81*
ZnSe(B3)	2.90 (2.8%)	2.56 (-9.2%)	-	2.74 (-2.8%)	2.82_{6K}
ZnTe(B3)	2.52 (5.4%)	2.19 (-8.4%)	-	2.38 (-0.4%)	2.39_{2K}
MgS(B1)	4.12 (-8.4%)	4.02 (-10.7%)	-	4.07 (-9.6%)	4.50_{77K}
MgS(B3)	5.18 (-4.1%)	-	-	-	5.40^{a}_{5K}
MgTe(B3)	3.59 (-2.2%)	-	-	-	3.67^{b}_{2K}
CaO(B1)	7.55 (-3.2%)	6.97 (-10.6%)	-	7.31 (-6.3%)	7.80^{*+}
CuCl(B3)	2.00 (-41%)	1.72 (-49.3%)	1.78 (-47.5%)	1.85 (-49.3%)	3.39_{2K}
CuBr(B3)	1.83 (-40.4%)	1.62 (-47.2%)	1.68 (-45.3%)	1.71 (-44.3%)	$3.07_{1.6K}$
AgF(B1)	1.80 (-35.7%)	2.44 (-12.9%)	-	2.22 (-20.7%)	$2.80_{4.8K}$
AgI(B1)	2.72 (-6.5%)	2.83 (-2.7%)	-	2.77 (-4.8%)	2.91_{4K}
GaN(B4)	3.13 (-5.2%)	3.13 (-5.2%)	-	3.13 (-5.2%)	3.30^{c}_{10K}
InN(B4)	0.82 (15.5%)	0.82 (15.5%)	-	0.82 (15.5%)	0.71^{d}_{10K}
AlN(B4)	5.52 (-10.8%)	5.53 (-10.7%)	5.56 (-10.2%)	5.53 (-10.7%)	6.19^{e}_{7K}
ZnO(B4)	2.77 (-19.5%)	2.77 (-19.5%)	2.72 (-20.9%)	2.76 (-19.7%)	3.44*
LiF(B1)	13.80 (1.5%)	12.92 (-5.0%)	-	13.40 (-1.5%)	13.6^{f}_{300K}
BP(B3)	1.80 (-10.0%)	1.87 (-6.5%)	-	1.83 (-8.5%)	2.00_{300K}
BN(B3)	5.86 (-5.5%)	5.83 (-6.0%)	-	5.85 (-5.6%)	6.20_{300K}
MgSe(B1)	2.95 (19.4%)	2.84 (15.0%)	-	2.89 (17.0%)	2.47_{300K}
BaS(B1)	3.23 (-16.8%)	3.37 (-13.1%)	-	3.31 (-14.7%)	3.88_{300K}
BaSe(B1)	2.80 (21.8%)	2.94 (-17.9%)	-	2.87 (-19.8%)	3.58_{300K}
BaTe(B1)	2.13 (-30.8%)	2.34 (-24.0%)	-	2.24 (-27.3%)	3.08_{300K}
BAs(B3)	1.69 (15.8%)	1.75 (19.9%)	-	1.72 (17.8%)	1.46_{300K}

*Extrapolated values.$^{+}$Reported value are direct gap at Γ.[a]Ref [34].[b]Ref. [35].

[d]Ref [36].[e]Ref [37]. [f]Ref [38]. [c]Ref. [39].

TABLE V. Band gap error statistics for compounds of Tables IV, in eV. (See text)

Error relative to LT experiments.				
	mBJ(a_{LDA})	mBJ(a_{GGA})	mBJ(a_{Prom})	mBJ(a_{LT})
ME[a]	-0.15	-0.32	-0.24	-0.87
MAE[b]	0.33	0.35	0.30	0.45
SD[c]	0.44	0.43	0.42	1.99
Error relative to RT experiments.				
	mBJ(LDA)	mBJ(GGA)	mBJ(a_{Prom})	
ME[a]	-0.25	-0.30	-0.27	
MAE[b]	0.48	0.47	0.44	

[a] Mean error. [b] Mean absolute error. [c] Standard deviation.

We finally present in Table V, the statistical analysis of the gap value obtained from a band structure calculation using mBJLDA potential using as input different lattice parameter obtained from different optimization procedures. The use of the average lattice parameter give clearly the best result . It is worth noting that when the experiment parameter at low temperature, mBJ(a_{LT}), is introduced in the code to calculate the band gap values, we get, in some cases, very deviation form the experimental value that are not expected, in principle.

V. CONCLUSIONS

We have calculated using the mBJLDA potential proposed recently [2], the band structure of forty one semiconductors and got the band gap value which we compared to experiment. Since there is no expression for the exchange and correlation energy so that the mBJLDA potential can be obtained from it as in the usual theory, the corresponding optimization procedure neglects by force this term in the energy functional. In principle therefore to fit an energy vs volume curve to an equation of states as a Murnaghan expression is quite disputable. Nevertheless, if we explore the result it turns out that the minimum value of the curve and its position do not deviate in an important way from experiment. The result of the Bulk modulus and its derivative with respect to pressure is, nevertheless, totally wrong. We have calculated the electronic band structure of all the forty one semiconductors considered. As an overall first sight picture, the new potential causes a rigid displacement of the conduction band towards higher energies so as to considerably improve the agreement with experiment of the band gap values. A closer look reveals that, in some cases, there are notifiable deviations from a rigid displacement of the band structure calculated with the previous version of the code that might result in wrong conclusions as it could happen when the band structure of an interface is calculated, for example. We explored at this point the resulting band gap predicted value as a function of the lattice parameter used. We found two important facts. first, the best result for the band gap value is obtained in general, if the average lattice parameter, a_{Avg}, is used ($a_{Avg} = (a_{LDA} + a_{GGA})/2$) where $a_{LDA}(a_{GGA})$ is the lattice parameter that result from an LDA(GGA) optimization. Another important result is that if we take the experimental lattice parameter into the code using the mBJLDA potential, important deviation from the experimental gap value are obtained, a result to bear in mind for a detailed analysis of the performance of the new mBJLDA potential. This result is important since it shades the optimization procedure in the sense that a lattice parameter closer to experiment does not guarantee a better prediction for the band gap. In spite of the above observations, our work shows that for the forty one semiconductors considered the new potential represents a very important improvement as compared to the results obtained from the previous version of the code. We find, nevertheless, that there are still important issues to be fixed before we consider the proper prediction of the band gap value of semiconductors, a closed problem.

---

[1] P. Blaha, K. Schwars, G.K.H. Madsen, D. Kvasnicka, and J. Luitz, *WIEN2K:Full Potential-Linearized Augmented Plane waves and Local Orbital Programs for Calculating Crystal Properties*, edited by K. Schwars, Vienna University of Technology, Austria, (2001).
[2] F. Tran and P. Blaha, *Phys. Rev. Lett.* **102**, 226401 (2009)
[3] G. K. H. Madsen, P. Blaha, K. Schwarz, E. Sjstedt, and L. ordstrm, *Phys. Rev. B* **64**, 195134 (2001).
[4] P. Hohenberg and W. Khon, *Phys. Rev.* **136**, B864 (1964).
[5] W. Khon and L.J. Sham, *Phys. Rev.* **140**, A1133 (1965).
[6] J.P. Perdew and Y. Wang, *Phys. Rev. B* **45**, 13244 (1992).

[7] J.P. Perdew, S. Kurth, J. Zupan, and P. Blaha, *Phys. Rev. Lett.* **82**, 2544 (1999).
[8] A.D. Becke and E.R. Johnson, *J. Chem.* **124** 221101 (2006).
[9] A. D. Becke and M.R. Roussel, *Phys. Rev. A* **39**, 3761 (1989).
[10] Murnaghan F.D., *Am. J. Math* **59**, 235 (1937).
[11] F. Birch, *Phys. Rev.* **71** 809 (1947)
[12] D. M. Teter, G. V. Gibbs, M. B. Boisen, Jr., D. C. Allan, M. P. Teter, *J. Chem. Phys.* 123, 174101 (1995).
[13] M. L. Cohen, *Phys. Rev. B,* **32**, 798 (1985).
[14] P.E. Van Camp, V.E. Van Doren, and J. T. Devreese, *Phys. Rev. B* **38**, 12675 (1988).
[15] Yingwei Fei, *American Mineralogist* **84**, 272 (1999).
[16] R.A. Miller and Charles S. Smith, *J. of Phys. and Chem. of Sol.* **25**, 1279 (1964).
[17] V. Fiorentini, *Phys. Rev. B* **46**, 2086 (1992).
[18] J. V. Aleksandrov, A. F. Goncharov, S. M. Stishov, and E. Y. Yakovenko, *JETP Lett.* **50**, 127 (1989).
[19] S-H. Wei and A. Zunger, *Phys. Rev. B* **60** , 5404 (1999).
[20] D. H. Yean and J. R. Riter, *J. Phys. Chem. Solids*, **32** 653 (1971).
[21] A. Zaoui, and F. El Haj Hassan, *Superlattices and Microstructures*, **32**, 91 (2002).
[22] H. J. McSkimin, A. Jayaraman. P. Andreatch, *J. Appl. Phys.* **38**, 2362 (1967).
[23] S. Adachi, *Handbook on Physical Properties of Semiconductors, Vols. I, II and III.* Kluwer Academic Publishers (2004).
[24] O. Madelung, *Data in Sciene and Technology, Semiconductors Group IV Elements and II-V Compounds.* Ed. Springer-Verlag (1991).
[25] O. Madelung, *Semiconductors: Data Handbook CD-ROM.* Ed. Springer-Verlag (2003).
[26] J. N. Plendl and L. C. Mansur, *Appl. Opt.* **11**, 1194 (1972).
[27] A. Taylor and R. M. Jones, *in Silicon Carbide, A High Temperature Semiconductor*, edited by J. R. O'Connor and J. Smiltens (Pergamon, London, 1960), p. 1470.
[28] J.L. Staudenmann, R. D. Horning, R. D. Knox, D. K. Arch, and J. L. Schmit, *Appl. Phys. Lett.* **48**, 994 (1986).
[29] A. Bouhemadou, R. Khenata, F. Zegrar, M. Sahnoun, H. Baltache and A.H. Reshak, *Comp. Mat. Sc.*, **2**, 263 (2006).
[30] W. M. Vim and R. J. Paff, *J. Appl. Phys.* **45**, 1456 (1974).
[31] R. R. Reeber, *J. Appl. Phys.* **41**, 5063 (1970).
[32] N. Wang, M. Rohlfing, P. Krüger, and J. Pollmann, *Phys.Rev. B* **67**, 115111 (2003).
[33] S. Antoci and L. Mihich, *Phys.Rev. B* **21**, 799 (1980).
[34] D. Wolverson, D. M. Bird C. Bradford, K. A. Prior, and B. C. Cavenett, *Phys. Rev. B*, **64**, 113203 (2001).
[35] K. Watanabe, M. Th. Litz, M. Korn, W. Ossau, A. Waag et al. *J. Appl. Phys.* **81**, 451 (1997).
[36] M. Feneberg, J. Daubler, K. Thonke, and R. Sauer. *Phys. Rev. B*, **77**, 245207 (2008).
[37] H.Morkoc, *Handbook of Nitride Semiconductors and Devices*, Ed. Wiley-VCH (2008).
[38] D.M. Roessler and W.C. Walker, *J. Phys. Chem. Solids*, **28**, 1507 (1967).
[39] G. Ramírez-Flores, H. Navarro-Contreras, A. Lastras-Martínez, R. C. Powell and J. E. Greene, *Phys. Rev. B* **50**, 8433 (1994).